



Cleaning of Capped Multi-Layer Samples and Cleaning with Hydrogen using the Evactron[®] De-Contaminator (P23)

Christopher G. Morgan and Ronald Vane

XEI Scientific, Inc., Redwood City, CA, USA



Overview of Talk

6/24/2011

- Description of Evactron De-Contaminator and remote (downstream) plasma cleaning
- Using oxygen-containing gas to clean EUV optics and substrates
 - Cleaning rates with room air
 - Results from CXRO
 - Results from U. Albany
 - Results from SEMATECH
- Cleaning with hydrogen

Evactron De-Contaminator

6/24/2011



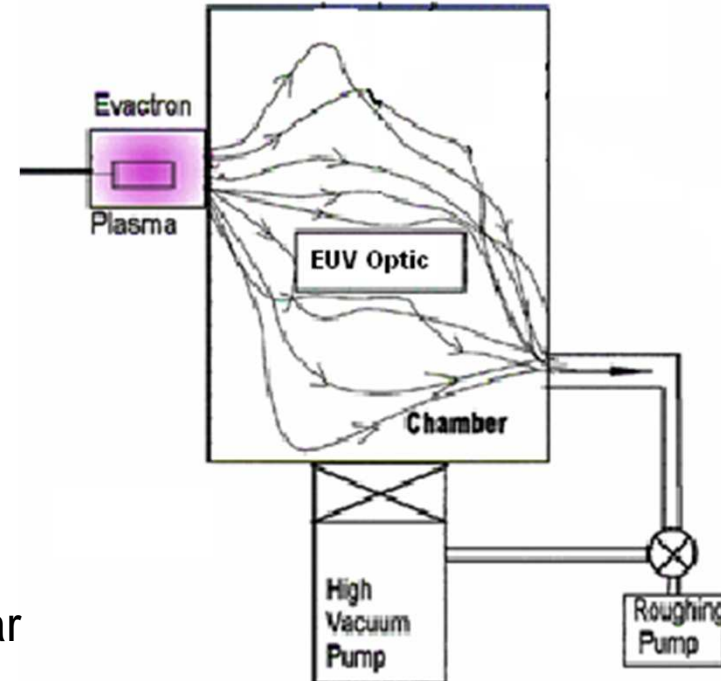
Plasma Radical Source (PRS) includes

- Valve assembly for metered flow of gas
- Pressure sensor
- RF impedance matching network
- Unique, patented RF electrode (not seen)

Remote (Downstream) Plasma Cleaning

6/24/2011

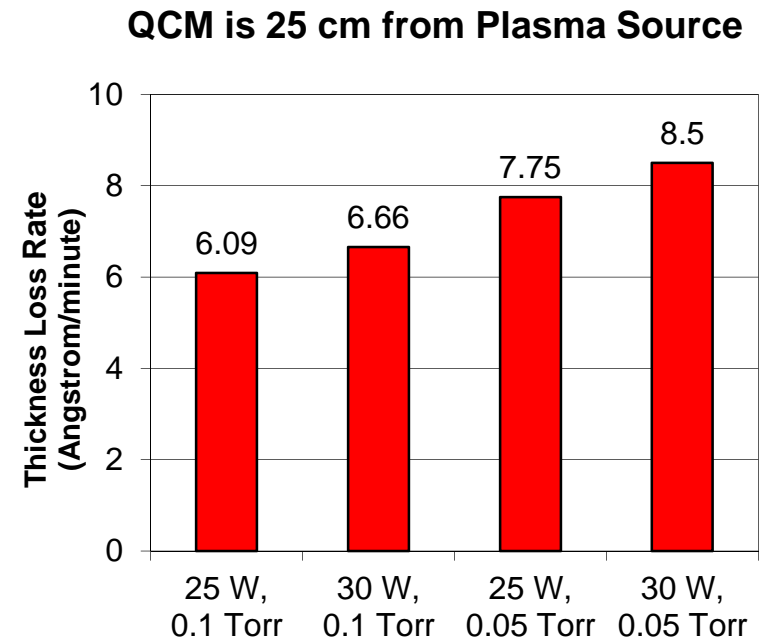
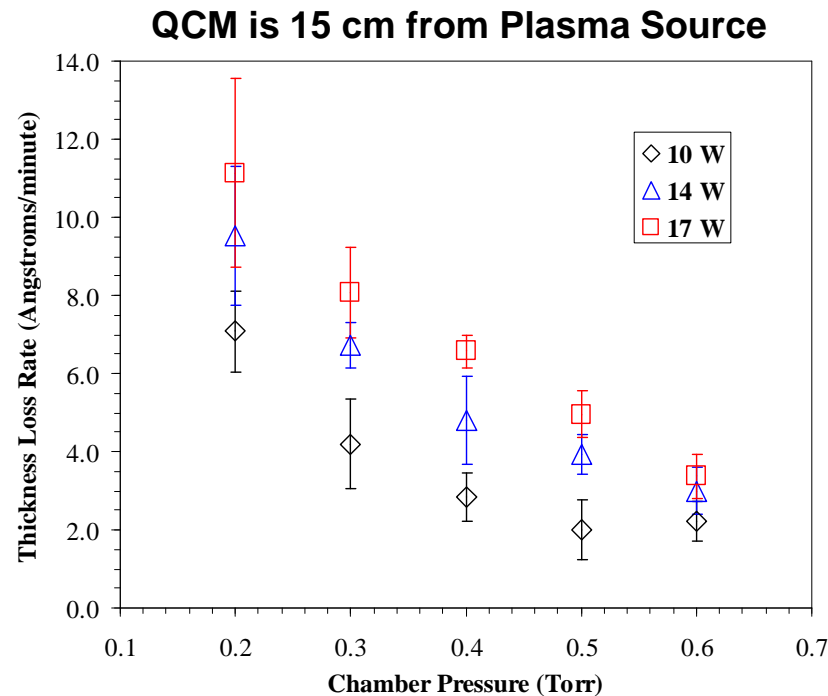
- The Evactron De-Contaminator is mounted on the left side of the chamber.
- In the Evactron Plasma, radicals are created.
- The radicals flow from the Evactron De-Contaminator to the pump port.
- The radicals chemically react *inside the chamber* with any hydrocarbon contamination they encounter.
- The plasma is confined to the region near where the Evactron De-Contaminator is mounted. Beyond this region, the temperature increase is $<5^{\circ}\text{C}$





Cleaning Rates with Room Air

6/24/2011

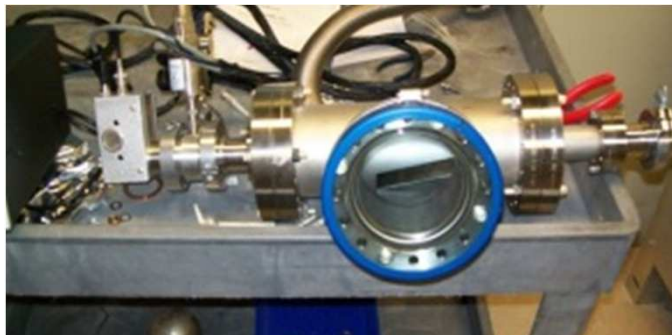


- Data taken using Quartz Crystal Microbalances (QCMs) coated with a thin layer (10-50 nm) of hydrocarbon contamination (pump oil).
- Cleaning rates *increase* as *pressure decreases* and *RF power increases*.
- Cleaning rates *decrease* as the *distance* between the cleaning target and the plasma source *increases*.

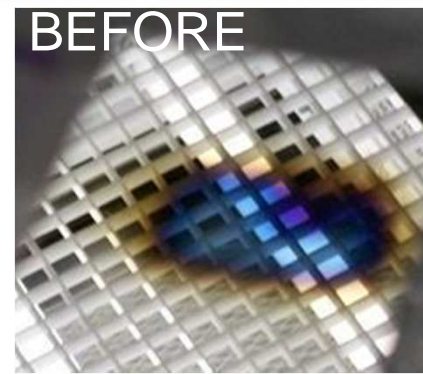


Cleaning Si-capped EUV Optics

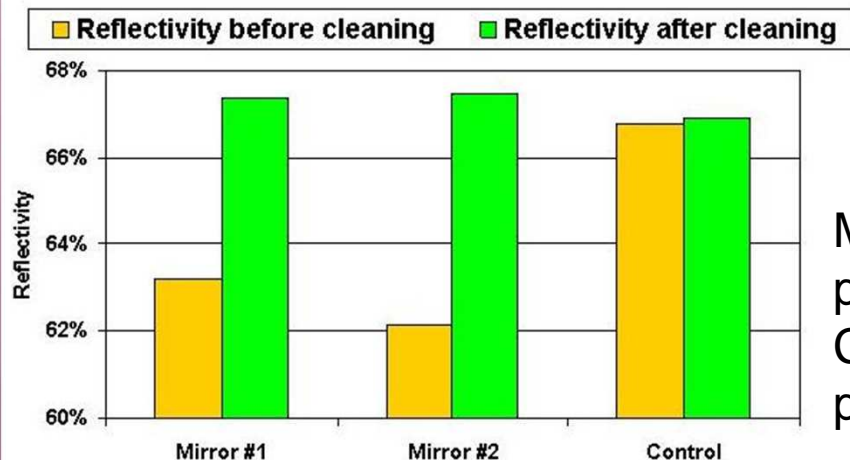
6/24/2011



Test chamber at CXRO used for cleaning Si-capped EUV optics



Senajith B. Rekawa, Paul E. Denham,
Brian H. Hoef, Michael S. Jones, and
Patrick P. Naulleau
Center for X-Ray Optics
Lawrence Berkeley National Laboratory



ML mirrors (#1 & #2) are contaminated prior to Evactron cleaning.
Control mirror was uncontaminated prior to Evactron cleaning.



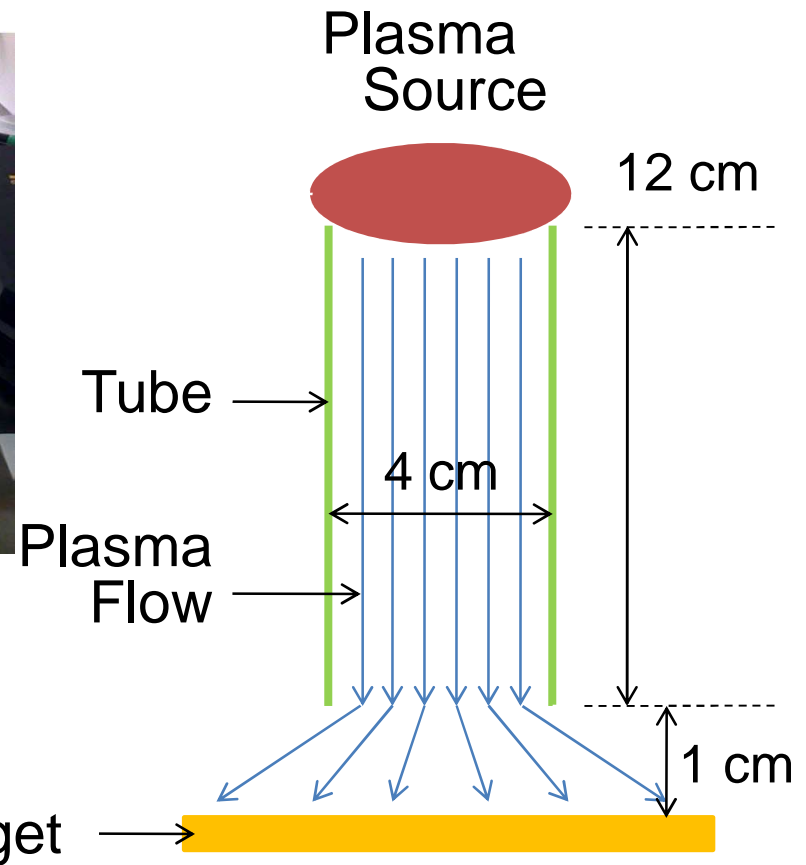
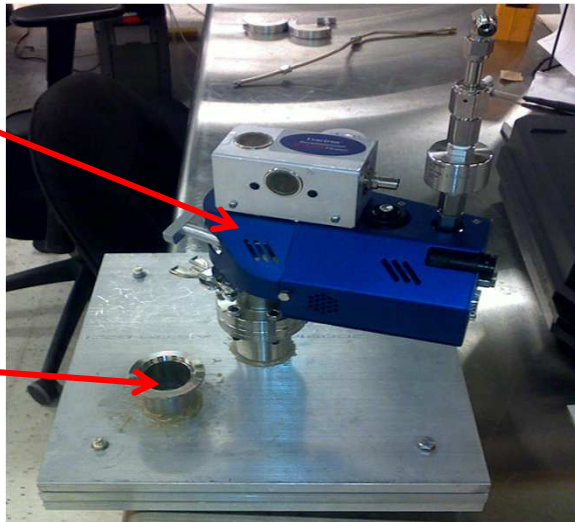
Cleaning Resist with Oxygen/Argon

6/24/2011

Evactron Cleaning of PMMA Resist on Si Wafer

Evactron DC located at the center of mask chamber

Exhaust Port



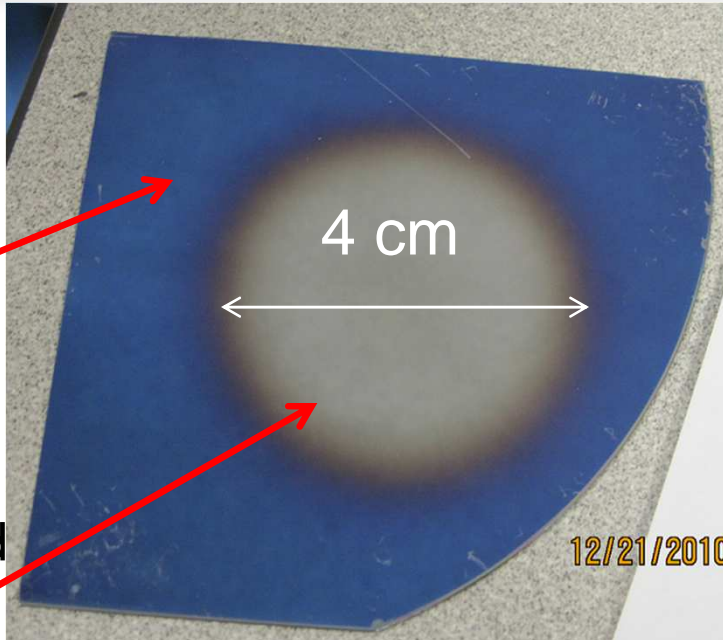
Mihir Upadhyaya and Greg Denbeaux
College of Nanoscale Science and
Engineering, University at Albany



Cleaning Resist with Oxygen/Argon

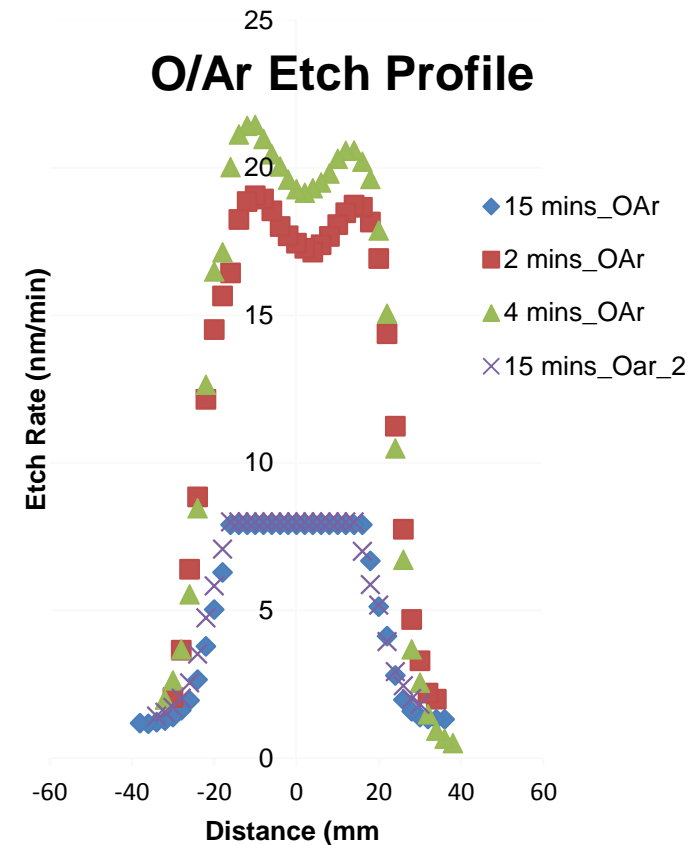
6/24/2011

Resist
Coated
Wafer



Plasma
Cleaned
Wafer

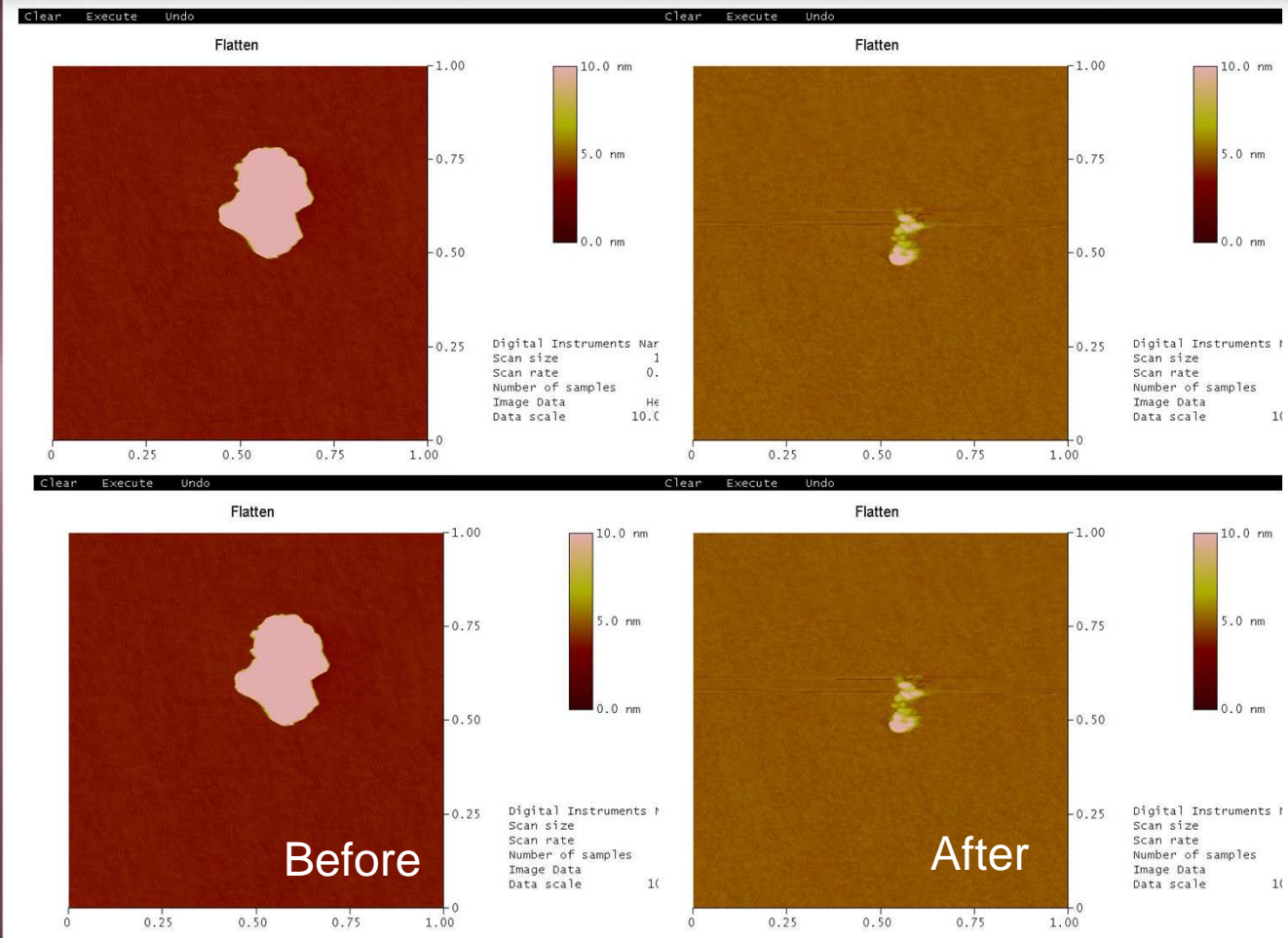
- Plasma Power = 20 W
- Plasma Pressure = 300 mTorr
- ~1/1 Oxygen/Argon mixture
- Cleaning Times: 4-15 minutes





Cleaning Quartz Mask Substrates

June 24, 2011



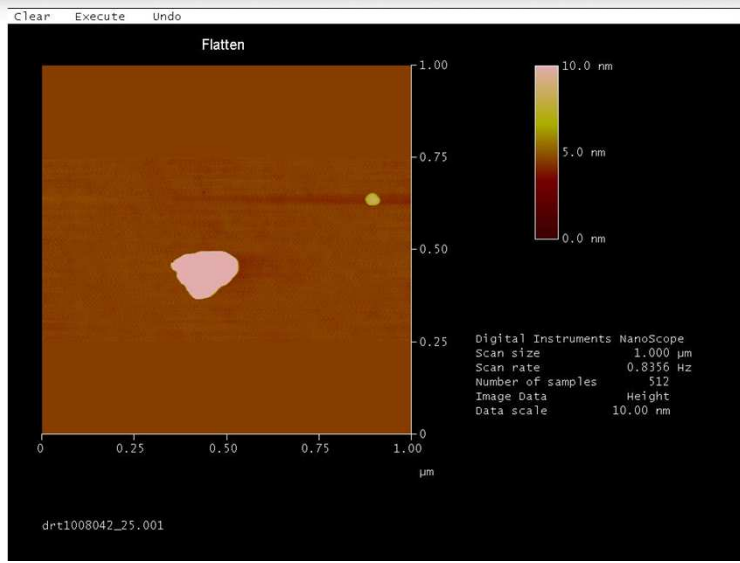
- Room air
- Pressure=300 mTorr
- Power=20 W.
- Time = 1 hr.
- No particle filter attached.
- Unacceptable amount of particles added during the process

Vibhu Jindal,
 Frank Goodwin,
 Patrick Kearney,
 SEMATECH,
 Albany, NY

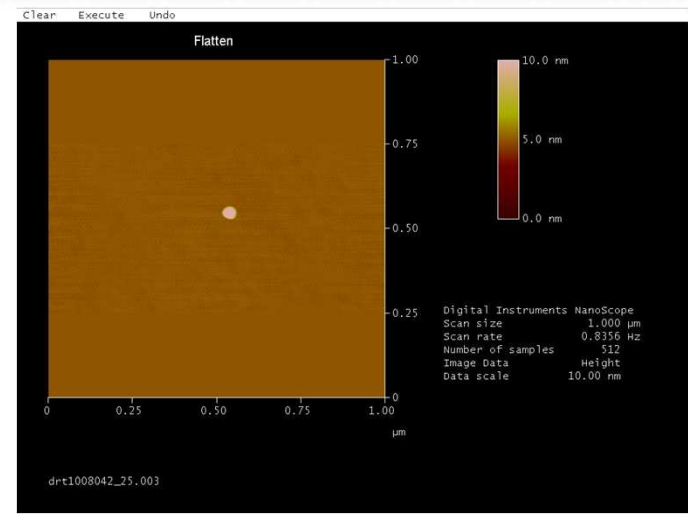


Cleaning Quartz Mask Substrates (cont.)

6/24/2011



Before



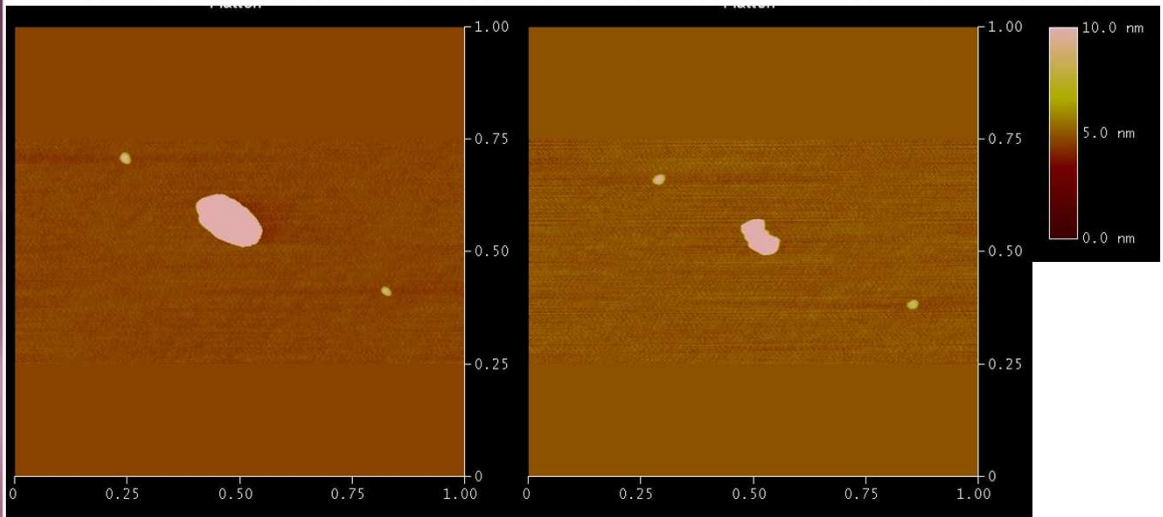
After

- Room air
- Pressure=250 mTorr
- Power=20 W.
- Time = 1 hr.



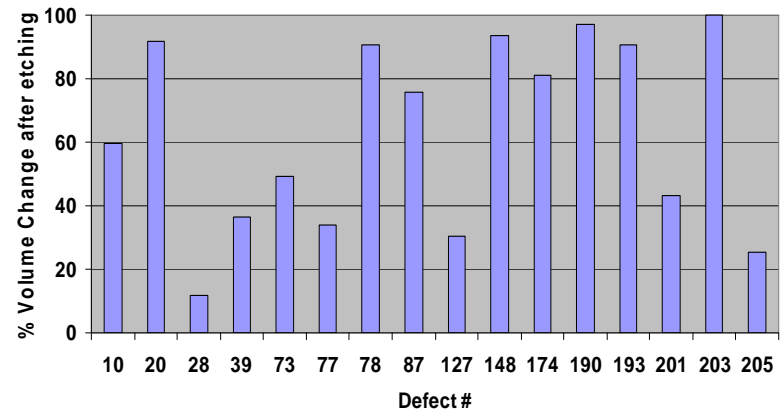
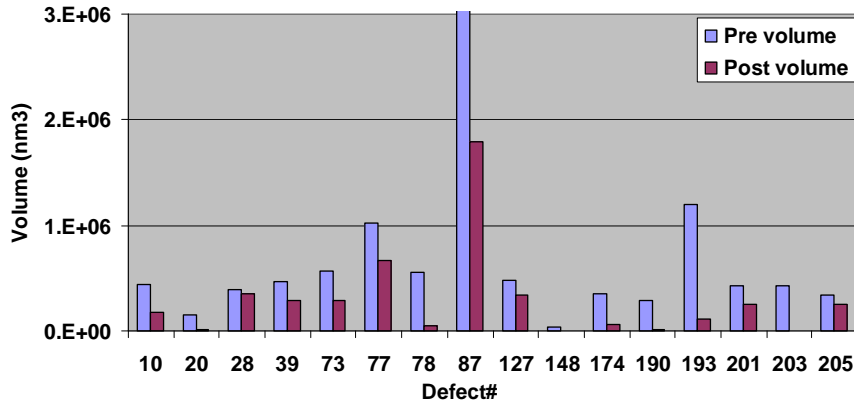
Cleaning Quartz Mask Substrates (cont.)

6/24/2011



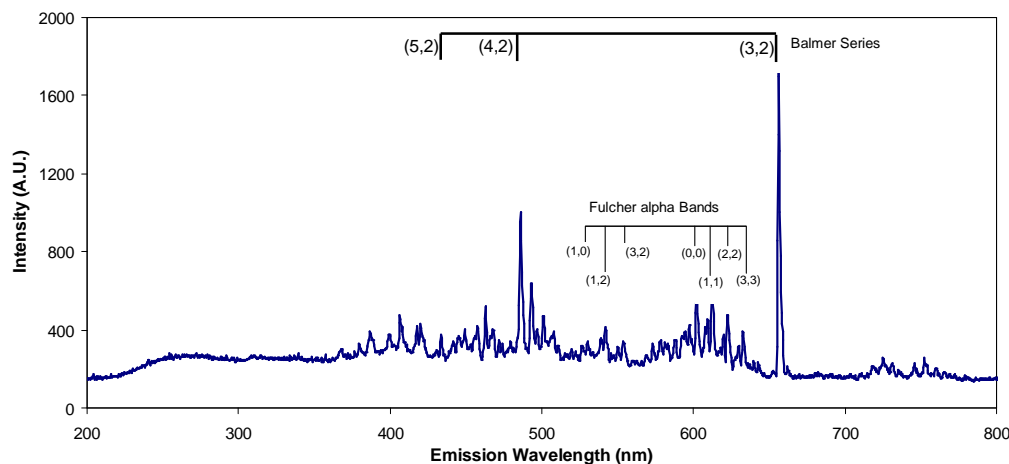
- Ar/O₂ (80/20) mixture
- Time=20 min
- Pressure=250mT
- Power=20W

Effect of plasma clean on C defects



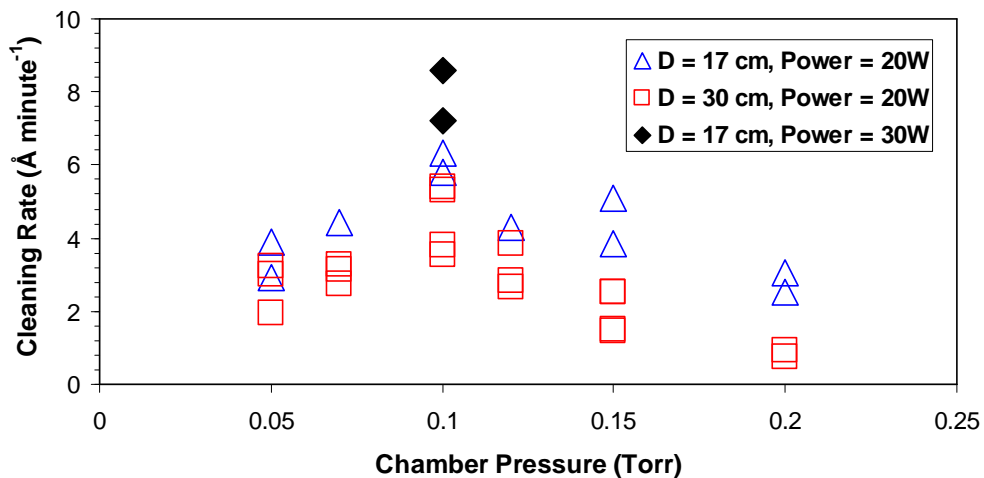
Cleaning with Hydrogen

6/24/2011



Emission Spectra:

- Pressure=100 mTorr
- Power=20W.
- The first three Balmer hydrogen transitions are seen in the spectrum, along with the Fulcher alpha bands
- Transitions due to N_2 , N_2^+ , OH, O, or NO are not seen



Cleaning Rates

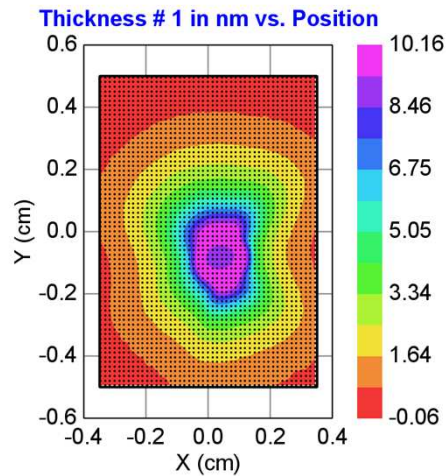
- Data taken using Quartz Crystal Microbalances (QCMs) coated with a thin layer (10-50 nm) of hydrocarbon contamination (pump oil).
- Maximum rate at 0.1 Torr



Cleaning with Hydrogen

6/24/2011

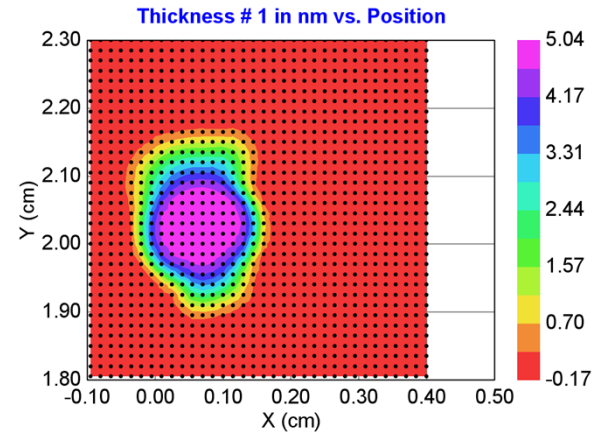
SPOT 1



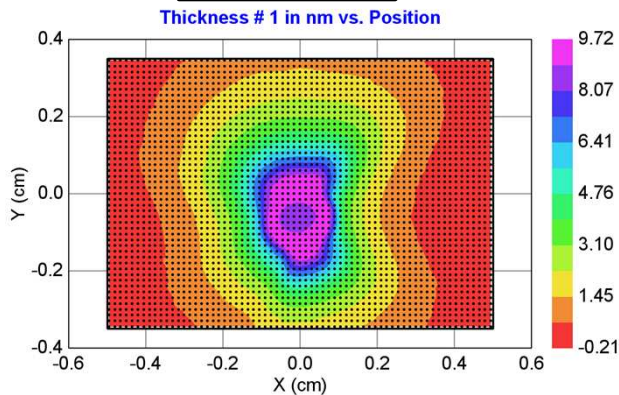
Resist contaminated sample
4 Hours cleaning
20 W
0.1 Torr

5 nm of cleaning in 4 hours

SPOT 1

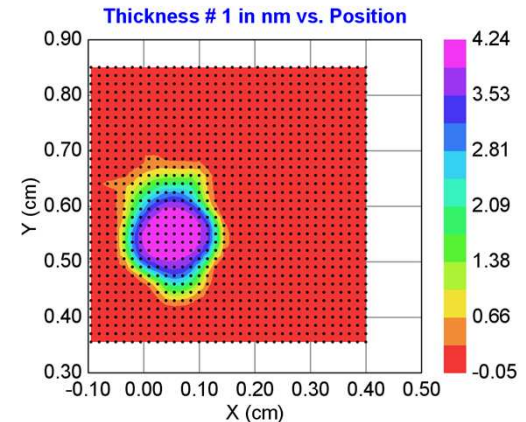


SPOT 2



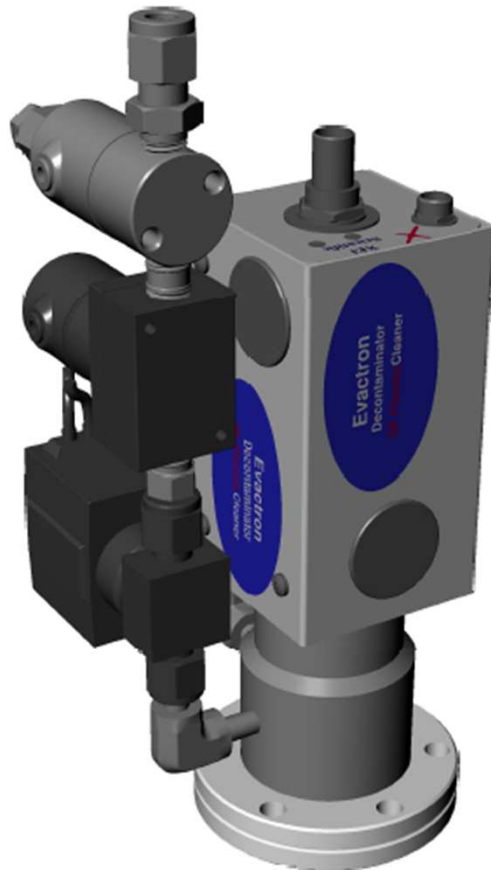
Mihir Upadhyaya and
Greg Denbeaux
College of Nanoscale
Science and
Engineering, University
at Albany

SPOT 2



New Evactron System for EUV Applications

6/24/2011



XEI will introduce a new system for end users and tool manufacturers in EUV Lithography. This system has been specifically developed to address EUV related cleaning challenges in high vacuum and clean room environments.

- Higher power RF generator (30 watts)
- Standard unit is used with hydrogen for oxygen sensitive cap layers
- Optional plasma source for use with oxygen for silicon-capped multi-layers and substrates
- Clean room compatible
- Contamination free operation
- Desktop or rack mounted configurations available



SUMMARY

6/24/2011

- Remote Plasma Cleaning with oxygen-containing gas has been shown to be effective in cleaning EUV optics and substrates.
 - Rates up to 0.85 nm/min with room air 25 cm away
 - Demonstrated cleaning results from external groups (CXRO, CNSE, and SEMATECH)
- Cleaning with hydrogen by remote plasma cleaning has been demonstrated.



FUTURE WORK

6/24/2011

- Continued work testing hydrogen to clean EUV components
- Development and testing of higher power sources to improve cleaning efficiency
- Research into working with plasma at lower pressures
- Development and testing of EUV specific system for ultraclean, high vacuum systems

Thank you



XEI Scientific, Inc.

Any Questions ?

Evactron De-Contaminator

6/24/2011



Plasma Radical Source (PRS) includes

- KF40 or CF275 fitting
- Valve assembly for metered flow of gas
- Pressure sensor
- RF impedance matching network
- Unique, patented RF electrode (not seen)



Controller includes

- Microprocessor control of PRS
- Compact 13.56 MHz RF generator
- 110-240 V, 50-60 Hz VAC
- External control with RS 232 serial connection – USB dongle available